Preferred Device

JFET - General Purpose Transistor

N-Channel

Features

• Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	25	Vdc
Reverse Gate-Source Voltage	V _{GS(r)}	-25	Vdc
Gate Current	I _G	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) (T _A = 25°C Derate above 25°C	P _D	225	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

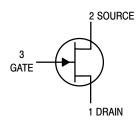
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.



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SOT-23 (TO-236) **CASE 318** STYLE 10

MARKING DIAGRAM



= Specific Device Code 6

М = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBF5457LT1	SOT-23	3000/Tape & Reel
MMBF5457LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u> </u>	•	1	•	
Gate–Source Breakdown Voltage (I _G = 10 μAdc, V _{DS} = 0)	V _(BR) GSS	-25	-	-	Vdc
Gate Reverse Current $(V_{GS} = 15 \text{ Vdc}, V_{DS} = 0)$ $(V_{GS} = 15 \text{ Vdc}, V_{DS} = 0, T_A = 100^{\circ}\text{C})$	I _{GSS}	- -	- -	-1.0 -200	nAdc
Gate Source Cutoff Voltage (V _{DS} = 15 Vdc, I _D = 10 nAdc)	V _{GS(off)}	-0.5	_	-6.0	Vdc
Gate Source Voltage (V _{DS} = 15 Vdc, I _D = 100 μAdc)	V _{GS}	_	-2.5	-	Vdc
ON CHARACTERISTICS	<u> </u>		•		
Zero-Gate-Voltage Drain Current (Note 2) (V _{DS} = 15 Vdc, V _{GS} = 0)	I _{DSS}	1.0	-	5.0	mAdc
SMALL-SIGNAL CHARACTERISTICS	<u> </u>	•	•	•	
Forward Transfer Admittance (Note 2) (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)	Y _{fs}	1000	-	5000	μmhos
Output Common Source Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)	lyosl	-	10	50	μmhos
Input Capacitance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 MHz)	C _{iss}	-	4.5	7.0	pF
Reverse Transfer Capacitance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 MHz)	C _{rss}	-	1.5	3.0	pF

^{2.} Pulse Test: Pulse Width ≤ 630 ms, Duty Cycle ≤ 10%.

TYPICAL CHARACTERISTICS

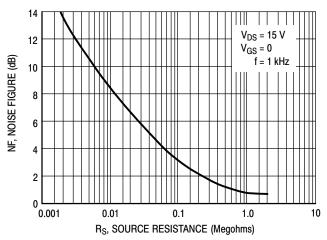


Figure 1. Noise Figure versus Source Resistance

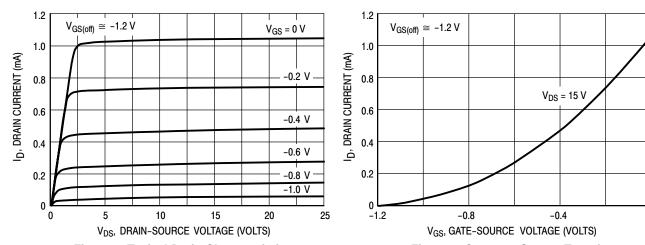


Figure 2. Typical Drain Characteristics

Figure 3. Common Source Transfer Characteristics

TYPICAL CHARACTERISTICS

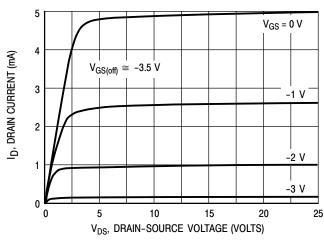


Figure 4. Typical Drain Characteristics

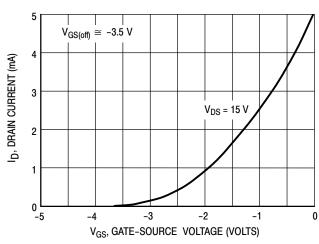


Figure 5. Common Source Transfer Characteristics

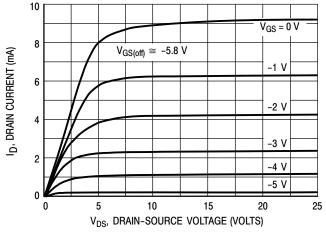


Figure 6. Typical Drain Characteristics

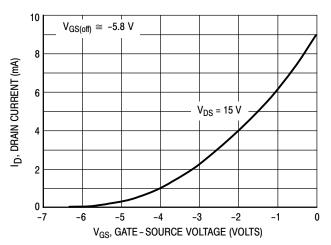


Figure 7. Common Source Transfer Characteristics

Note: Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%). Under dc conditions, self heating in higher I_{DSS} units reduces I_{DSS} .

MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40





SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024

MAX

1.11

0.10

0.50

0.20

3.04

1.40

2.04

0.55

0.69

2.64

10°





DETAIL "A" Scale 3:1







NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR			
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	2. CATHODE 2.	2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	2. ANODE 2.	3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT			STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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